SamHop Microelectronics Corp.

STS3409L

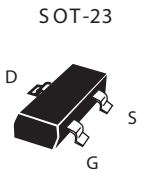
Ver 1.0

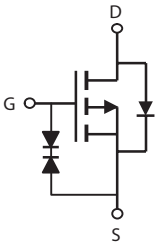
P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
-20V	-3.2A	75 @ VGS=-10V
		95 @ VGS=-4.5V
		137 @ VGS=-2.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- Suface Mount Package.





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		-20	V
V_{GS}	Gate-Source Voltage		±10	V
I_D	Drain Current-Continuous [a]	T_A=25°C	-3.2	A
		T_A=70°C	-2.6	A
I_{DM}	-Pulsed [b]		-12	A
P_D	Maximum Power Dissipation [a]	T_A=25°C	1.25	W
		T_A=70°C	0.8	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [a]	100	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-16V , V_{GS}=0V			-1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±10V , V_{DS}=0V			±10	uA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=-250uA	-0.5	-0.8	-1.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-10V , I_D=-1.6A		60	75	m ohm
		V_{GS}=-4.5V , I_D=-1.4A		75	95	m ohm
		V_{GS}=-2.5V , I_D=-1.2A		102	137	m ohm
g_{FS}	Forward Transconductance	V_{DS}=-5V , I_D=-1.6A		6.2		S
DYNAMIC CHARACTERISTICS [c]						
C_{ISS}	Input Capacitance	V_{DS}=-10V,V_{GS}=0V f=1.0MHz		298		pF
C_{OSS}	Output Capacitance			78		pF
C_{RSS}	Reverse Transfer Capacitance			69		pF
SWITCHING CHARACTERISTICS [c]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=-10V I_D=-1A V_{GS}=-10V R_{GEN}= 6 ohm		19		ns
t_r	Rise Time			27		ns
$t_{D(OFF)}$	Turn-Off Delay Time			22		ns
t_f	Fall Time			43		ns
Q_g	Total Gate Charge	V_{DS}=-10V,I_D=-1.6A,V_{GS}=-10V		11		nC
		V_{DS}=-10V,I_D=-1.6A,V_{GS}=-4.5V		5		nC
Q_{gs}	Gate-Source Charge	V_{DS}=-10V,I_D=-1.6A, V_{GS}=-10V		0.4		nC
Q_{gd}	Gate-Drain Charge			1.9		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=-0.5A		-0.8	-1.2	V

Notes

a.Surface Mounted on FR4 Board,t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.

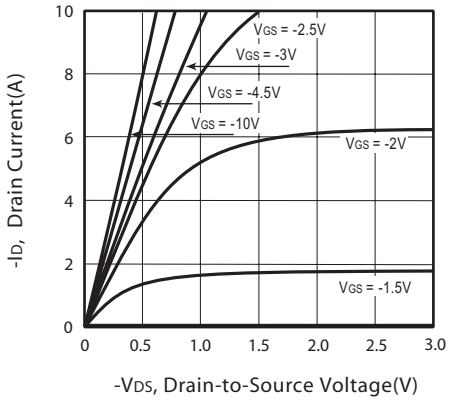


Figure 1. Output Characteristics

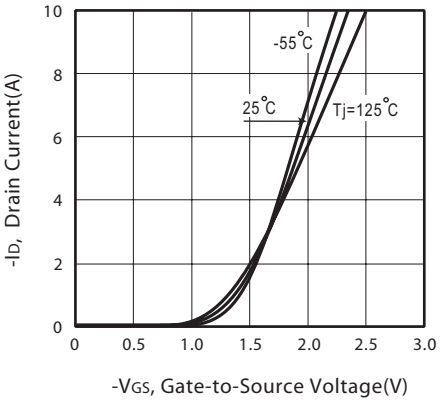


Figure 2. Transfer Characteristics

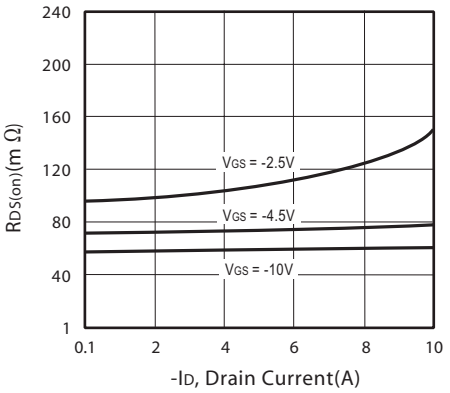


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

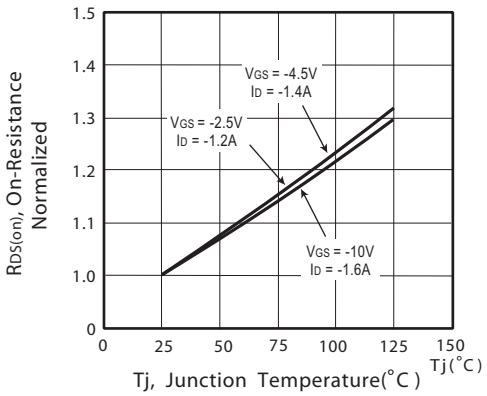


Figure 4. On-Resistance Variation with Drain Current and Temperature

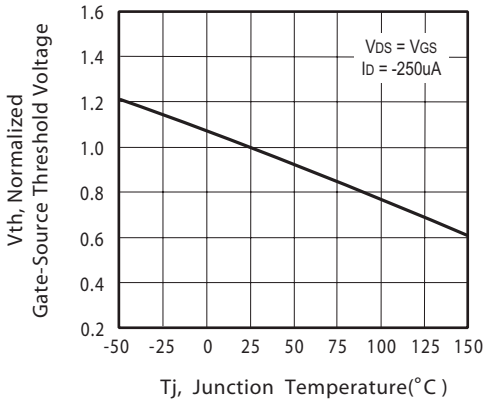


Figure 5. Gate Threshold Variation with Temperature

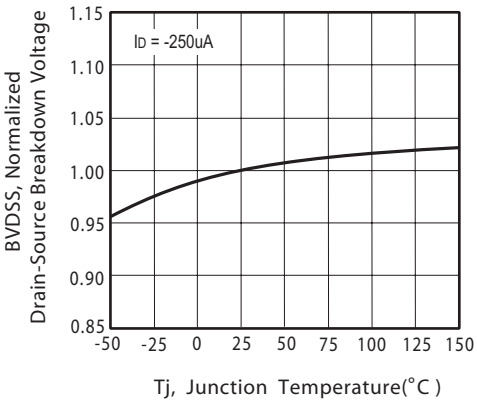


Figure 6. Breakdown Voltage Variation with Temperature

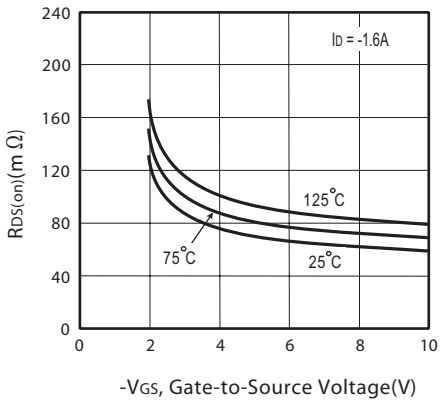


Figure 7. On-Resistance vs. Gate-Source Voltage

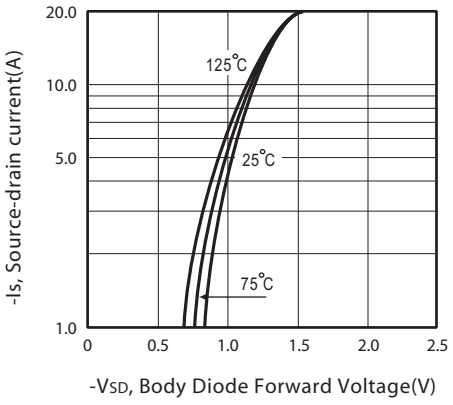


Figure 8. Body Diode Forward Voltage Variation with Source Current

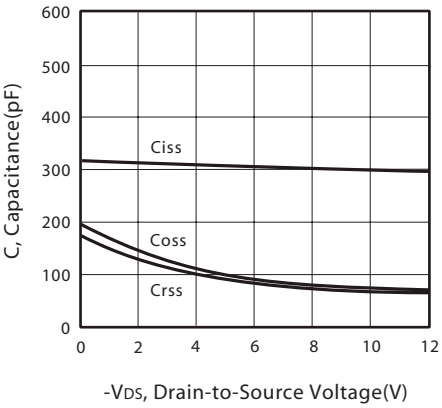


Figure 9. Capacitance

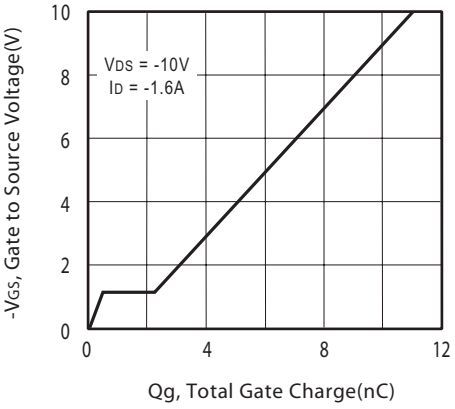


Figure 10. Gate Charge

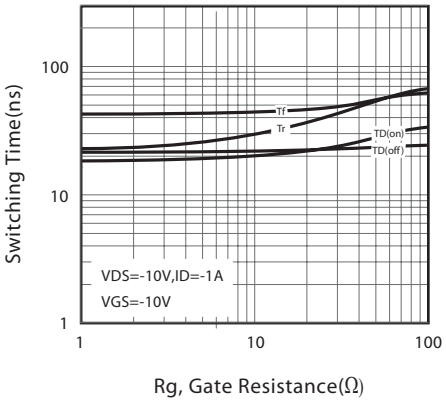


Figure 11. switching characteristics

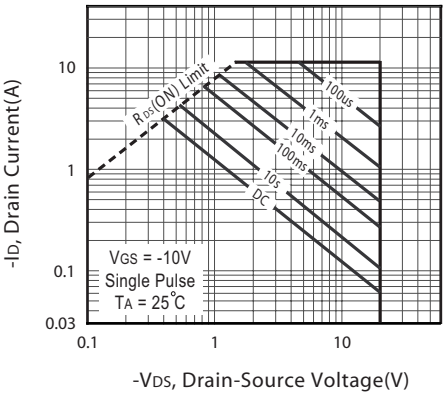


Figure 12. Maximum Safe Operating Area

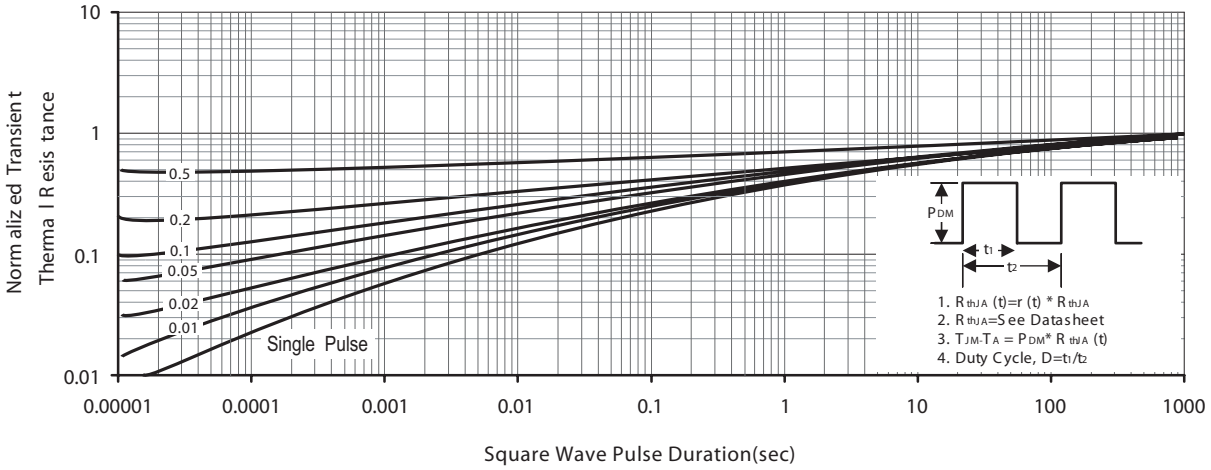
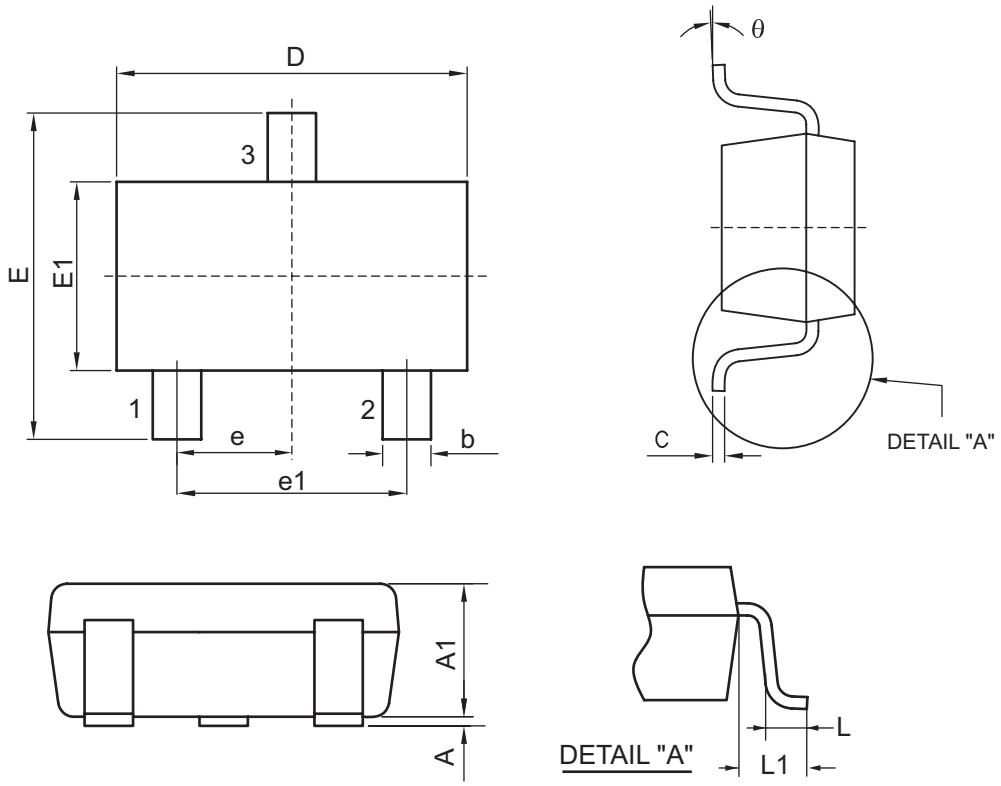


Figure 13. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

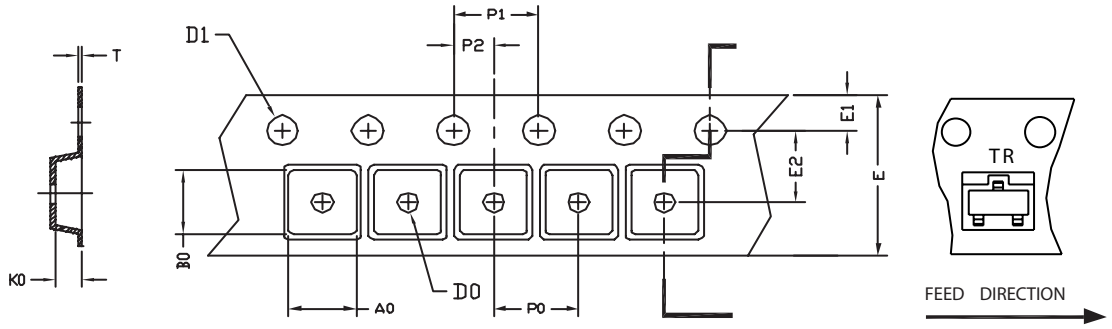
SOT 23



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.700	3.100	0.106	0.122
E	2.200	3.000	0.087	0.118
E1	1.200	1.700	0.047	0.067
e	0.850	1.150	0.033	0.045
e1	1.800	2.100	0.071	0.083
b	0.300	0.510	0.019	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.150	0.000	0.006
A1	0.887	1.300	0.035	0.051
L	0.450 REF.		0.018 REF.	
L1	0.600 REF.		0.024 REF.	
θ	0°	10°	0°	10°

SOT23 Tape and Reel Data

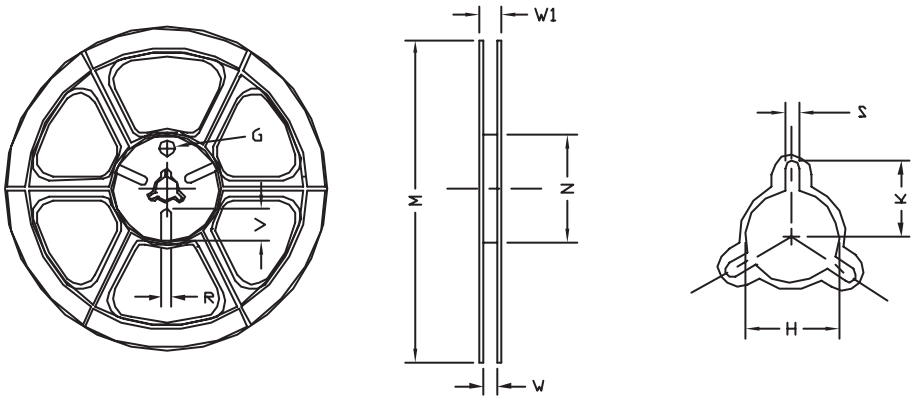
SOT23-3L Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT23-3L	3.15 ±0.10	2.77 ±0.10	1.22 ±0.10	ϕ 1.00 +0.05	ϕ 1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.22 ±0.04

SOT23-3L Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	ϕ 178	ϕ 178 ±1	ϕ 60 ±1	9.00 ±0.5	12.00 ±0.5	ϕ 13.5 ±0.5	10.5	2.00 ±0.5	ϕ 10.0	5.00	18.00